

## FEATURES

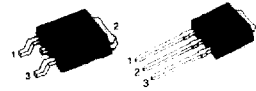
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = -200$ V
- Lower  $R_{DS(ON)}$  : 1.111  $\Omega$  (Typ.)

$$BV_{DSS} = -200 \text{ V}$$

$$R_{DS(on)} = 1.5 \Omega$$

$$I_D = -3.1 \text{ A}$$

**D-PAK**      **I-PAK**



1. Gate 2. Drain 3. Source

## Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	-200	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ\text{C}$ )	-3.1	A
	Continuous Drain Current ( $T_C=100^\circ\text{C}$ )	-1.96	
$I_{DM}$	Drain Current-Pulsed ①	-12	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	256	mJ
$I_{AR}$	Avalanche Current ①	-3.1	A
$E_{AR}$	Repetitive Avalanche Energy ①	3.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
$P_D$	Total Power Dissipation ( $T_A=25^\circ\text{C}$ ) *	2.5	W
	Total Power Dissipation ( $T_C=25^\circ\text{C}$ )	30	W
	Linear Derating Factor	0.24	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

## Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	4.17	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient *	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

\* When mounted on the minimum pad size recommended (PCB Mount).

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	-200	--	--	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
ΔBV/ΔT <sub>J</sub>	Breakdown Voltage Temp. Coeff.	--	-0.18	--	V/°C	I <sub>D</sub> =-250μA <b>See Fig 7</b>
V <sub>GS(th)</sub>	Gate Threshold Voltage	-2.0	--	-4.0	V	V <sub>DS</sub> =-5V, I <sub>D</sub> =-250μA
I <sub>GSS</sub>	Gate-Source Leakage, Forward	--	--	-100	nA	V <sub>GS</sub> =-30V
	Gate-Source Leakage, Reverse	--	--	100		V <sub>GS</sub> =30V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	--	--	-10	μA	V <sub>DS</sub> =-200V
		--	--	-100		V <sub>DS</sub> =-160V, T <sub>C</sub> =125°C
R <sub>DS(on)</sub>	Static Drain-Source On-State Resistance	--	--	1.5	Ω	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A ④
g <sub>fs</sub>	Forward Transconductance	--	2.2	--	∅	V <sub>DS</sub> =-40V, I <sub>D</sub> =-1.6A ④
C <sub>iss</sub>	Input Capacitance	--	415	540	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1MHz <b>See Fig 5</b>
C <sub>oss</sub>	Output Capacitance	--	70	105		
C <sub>rss</sub>	Reverse Transfer Capacitance	--	26	40		
t <sub>d(on)</sub>	Turn-On Delay Time	--	12	35	ns	V <sub>DD</sub> =-100V, I <sub>D</sub> =-3.5A, R <sub>G</sub> =18Ω <b>See Fig 13</b> ④ ⑤
t <sub>r</sub>	Rise Time	--	22	55		
t <sub>d(off)</sub>	Turn-Off Delay Time	--	33	75		
t <sub>f</sub>	Fall Time	--	15	40		
Q <sub>g</sub>	Total Gate Charge	--	15	19	nC	V <sub>DS</sub> =-160V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.5A <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
Q <sub>gs</sub>	Gate-Source Charge	--	3.3	--		
Q <sub>gd</sub>	Gate-Drain( " Miller " ) Charge	--	7.5	--		

## Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I <sub>S</sub>	Continuous Source Current	--	--	-3.1	A	Integral reverse pn-diode in the MOSFET
I <sub>SM</sub>	Pulsed-Source Current ①	--	--	-12		
V <sub>SD</sub>	Diode Forward Voltage ④	--	--	-5.0	V	T <sub>J</sub> =25°C, I <sub>S</sub> =-3.1A, V <sub>GS</sub> =0V
t <sub>rr</sub>	Reverse Recovery Time	--	125	--	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =-3.5A
Q <sub>rr</sub>	Reverse Recovery Charge	--	0.59	--	μC	di <sub>F</sub> /dt=100A/μs ④

### Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=40mH, I<sub>AS</sub>=-3.1A, V<sub>DD</sub>=-50V, R<sub>G</sub>=27Ω\*, Starting T<sub>J</sub>=25°C
- ③ I<sub>SD</sub> ≤ -3.5A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub>=25°C
- ④ Pulse Test : Pulse Width = 250μs, Duty Cycle ≤ 2%
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

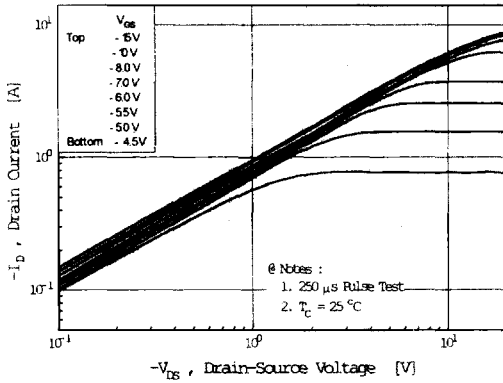


Fig 2. Transfer Characteristics

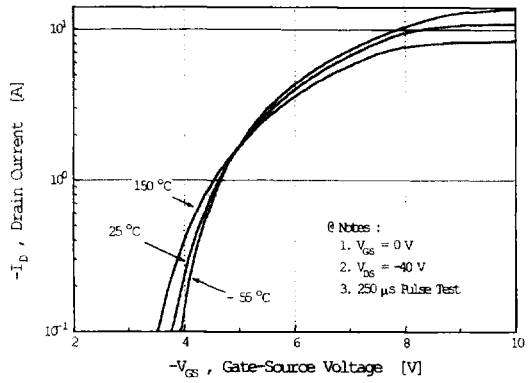


Fig 3. On-Resistance vs. Drain Current

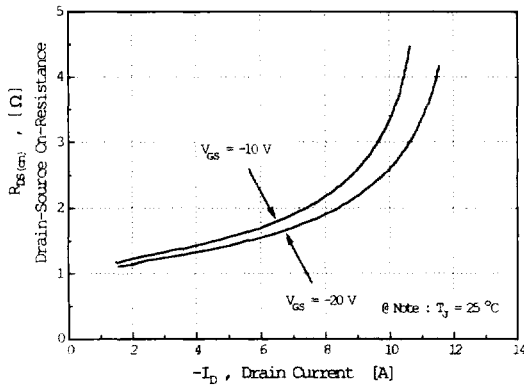


Fig 4. Source-Drain Diode Forward Voltage

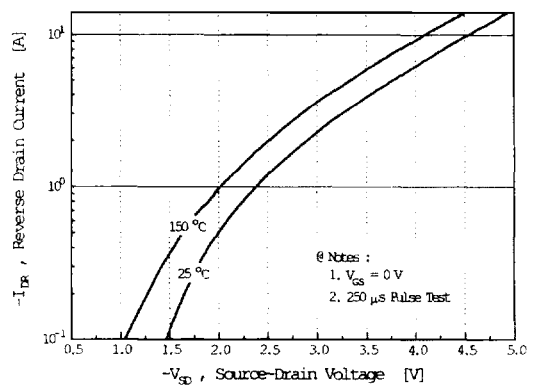


Fig 5. Capacitance vs. Drain-Source Voltage

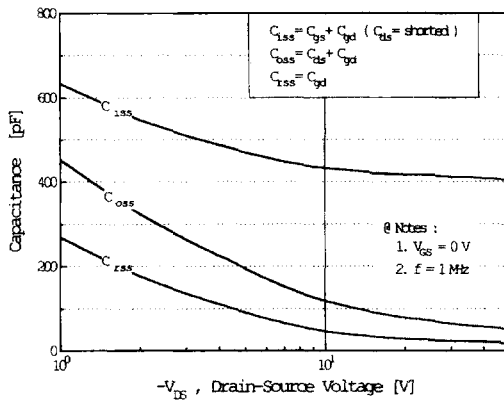
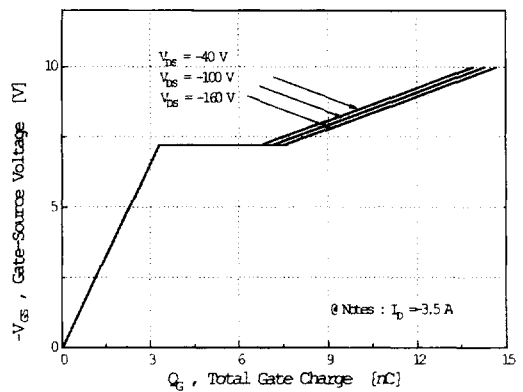
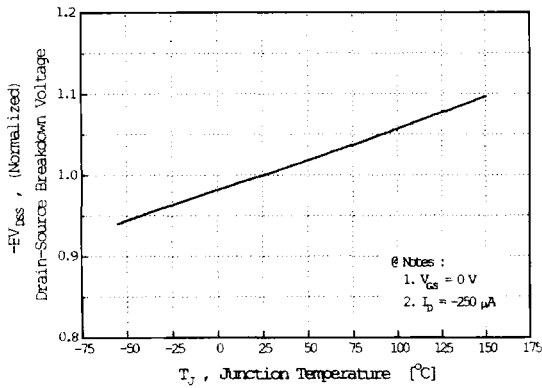


Fig 6. Gate Charge vs. Gate-Source Voltage

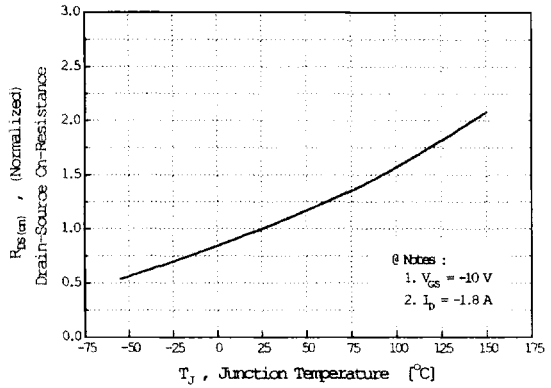


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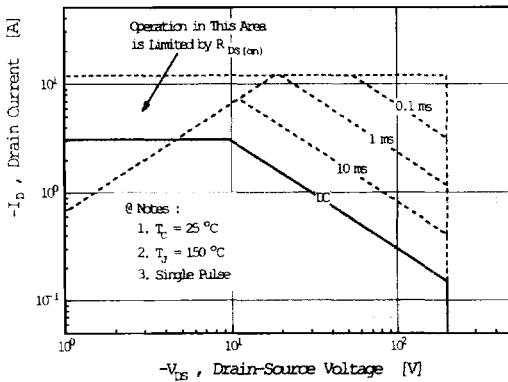
**Fig 7. Breakdown Voltage vs. Temperature**



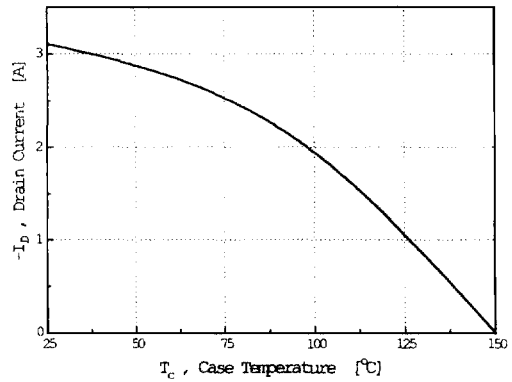
**Fig 8. On-Resistance vs. Temperature**



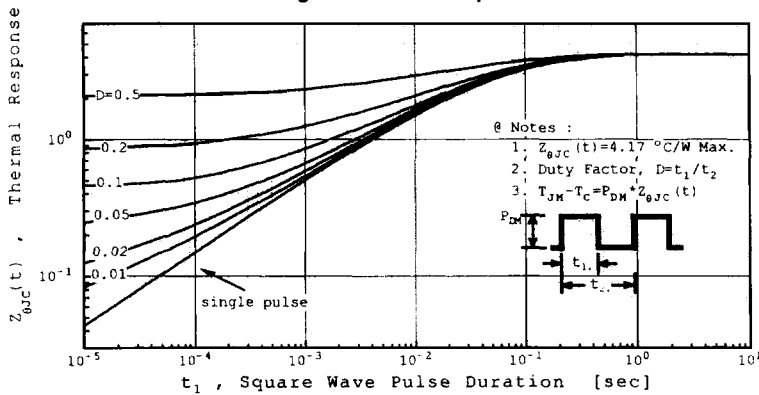
**Fig 9. Max. Safe Operating Area**



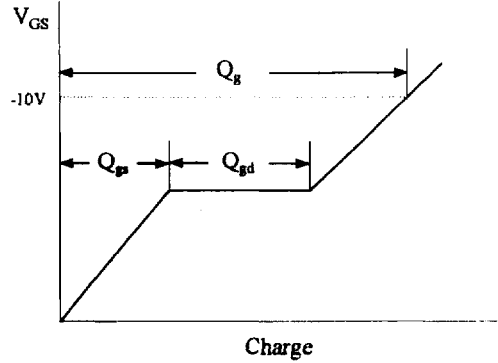
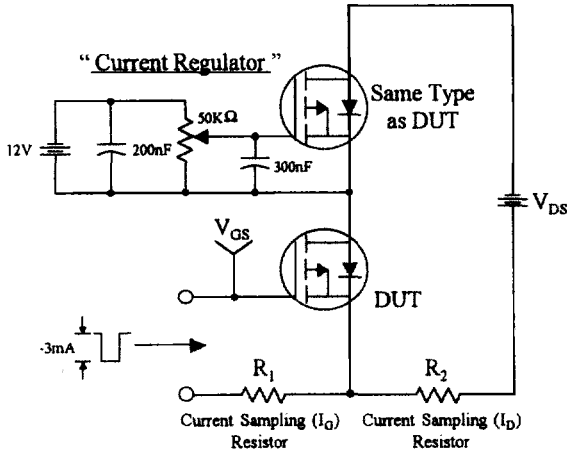
**Fig 10. Max. Drain Current vs. Case Temperature**



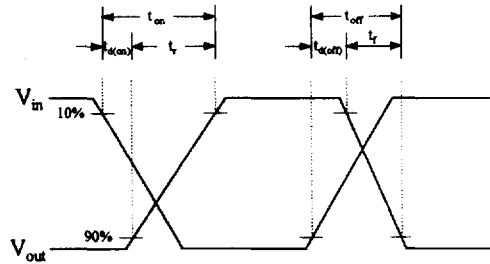
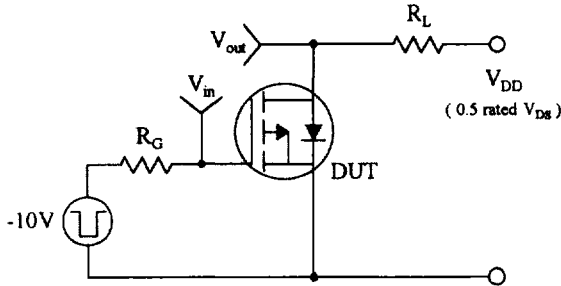
**Fig 11. Thermal Response**



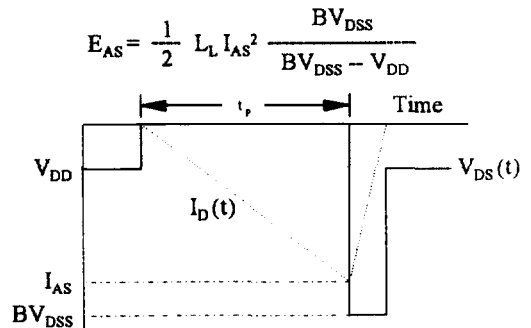
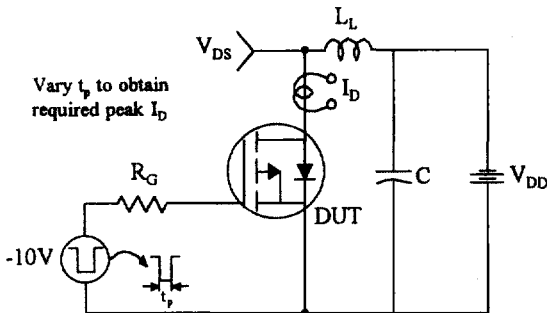
**Fig 12. Gate Charge Test Circuit & Waveform**



**Fig 13. Resistive Switching Test Circuit & Waveforms**



**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**



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Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

